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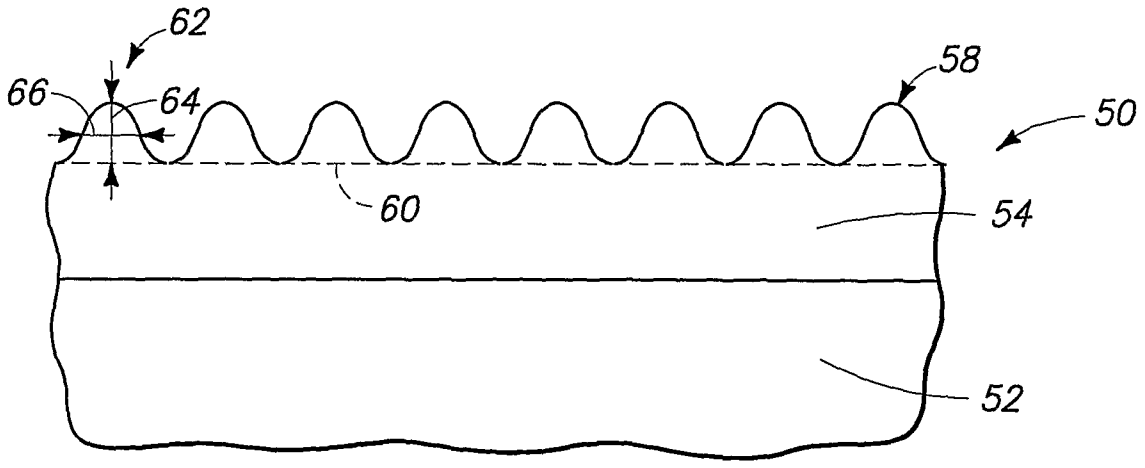
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(54) Title: CAPACITOR CONSTRUCTIONS, RUGGED SILICON-CONTAINING SURFACES, AND METHODS OF FORMING RUGGED SILICON-CONTAINING SURFACES



(57) Abstract: The invention encompasses a method of forming a rugged silicon-containing surface. A layer comprising amorphous silicon is provided within a reaction chamber at a first temperature. The temperature is increased to a second temperature at least 40^0 C higher than the first temperature while flowing at least one hydrogen isotope into the chamber. After the temperature reaches the second temperature, the layer is seeded with seed crystals. The seeded layer is then annealed to form a rugged silicon-containing surface. The rugged silicon-containing surface can be incorporated into a capacitor construction. The capacitor construction can be incorporated into a DRAM cell, and the DRAM cell can be utilized in an electronic system.

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— *with amended claims*

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